

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Yukihito OOWAKI et al.)
) Prior Application: Rule 53(b) Divisional of
) Serial No.:09/340,149
Serial No.: Not Yet Assigned) filed June 28, 1999
)
Filed: June 13, 2001) Prior Group Art Unit: 2814
)
) Prior Examiner: NGO, N.
)
For: MIS TRANSISTOR AND METHOD))
FOR PRODUCING SAME)

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 12, second full paragraph, lines 13-20, replace with the following:

A²
~Then, as shown in FIG. 3C, after a thin sacrificial oxide film 11 is laminated on the surfaces of the SiO₂ film 9 and the groove 4 of the silicon substrate, a polycrystalline silicon 10 is